

Title (en)

INDIUM-TIN-OXIDE (ITO) LAYER AND METHOD FOR PRODUCING THE SAME

Title (de)

INDIUM-ZINN-OXID (ITO)-SCHICHT UND VERFAHREN ZUR HERSTELLUNG DERSELBEN

Title (fr)

COUCHE D'OXYDE D'ETAIN ET D'INDIUM (ITO) ET SON PROCEDE DE PRODUCTION

Publication

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Application

**EP 01933932 A 20010504**

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Abstract (en)

[origin: WO0186731A1] The invention relates to a method for precipitating transparent and conductive indium-tin-oxide (ITO) layers, which have a particularly low resistance of preferably less than 200 mu OMEGA cm and a low degree of surface roughness of preferably less than 1 nm, onto a substrate. To this end, a combined HF/DC sputtering of an indium-tin-oxide (ITO) target is used in which an Ar/H<sub>2</sub> mixture serving as a reaction gas is fed to the process gas during sputtering. The invention also relates to (ITO) layers having the aforementioned properties.

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